

General Purpose Transistors

NPN Silicon

FEATURE

- High current capacity in compact package.
 $I_c = 1.5A$.
- Epitaxial planar type.
- NPN complement: LH8050
- Pb-Free Package is available.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
(S-)LH8050PLT1G	KEO	3000/Tape&Reel
(S-)LH8050PLT3G	KEO	10000/Tape&Reel
(S-)LH8050QLT1G	KEY	3000/Tape&Reel
(S-)LH8050QLT3G	KEY	10000/Tape&Reel

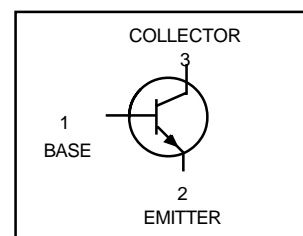
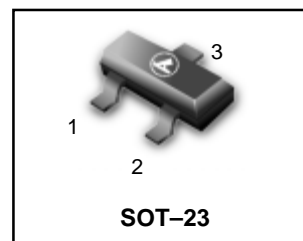
MAXIMUM RATINGS

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	50	V
Collector-Base Voltage	V_{CBO}	50	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current-continuoun	I_c	1500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Dissipation Power	P_D	225	mW
Junction and Storage Temperature	T_j, T_{stg}	-55 to +150	°C

LH8050PLT1G
Series
S-LH8050PLT1G
Series



LH8050PLTIG Series , S-LH8050PLTIG Series

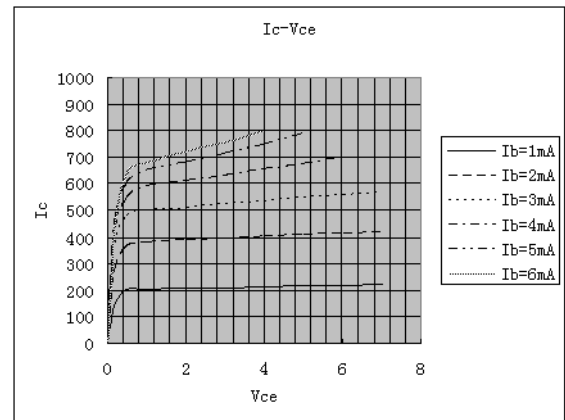
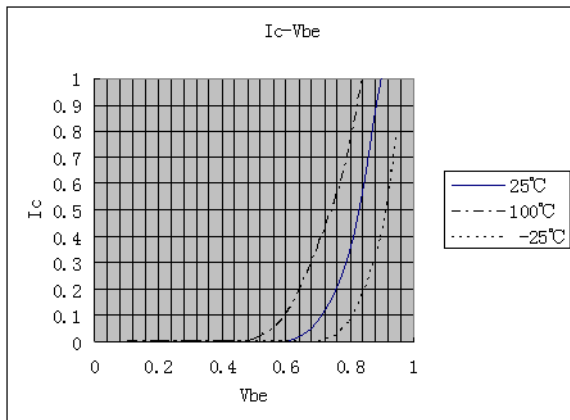
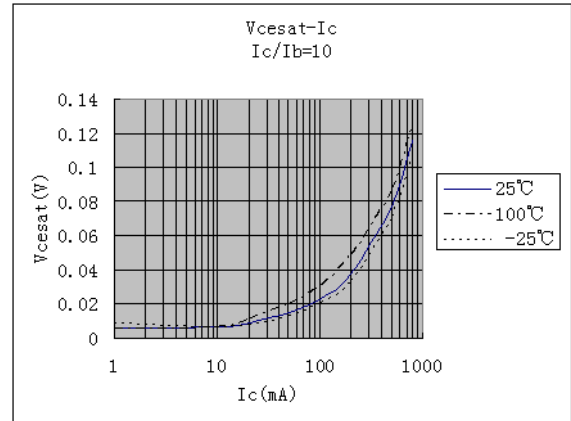
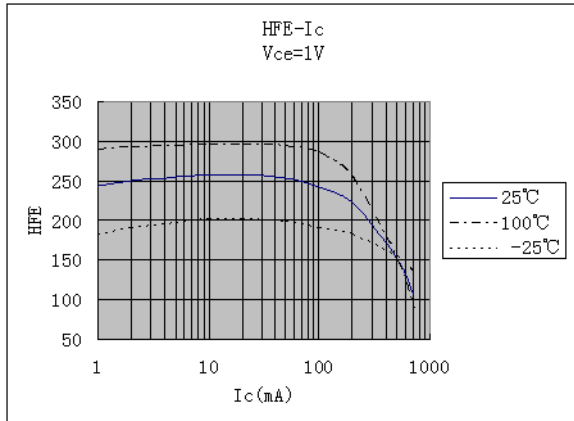
ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage (I _C =2.0mA, I _B =0)	V _{(BR)CEO}	50	-	-	V
Emitter-Base Breakdown Voltage (I _E =100μA, I _C =0)	V _{(BR)EBO}	6	-	-	V
Collector-Base Breakdown Voltage (I _C =100μA, I _E =0)	V _{(BR)CBO}	50	-	-	V
Collector Cutoff Current (V _{CB} =35V, I _E =0)	I _{CBO}	-	-	100	nA
Emitter Cutoff Current (V _{EB} =6V, I _C =0)	I _{EBO}	-	-	100	nA
Base-Emitter Voltage (V _{CE} =1V, I _C =10mA)	V _{BE}	-	0.66	1	V
DC Current Gain I _C =100mA, V _{CE} =1V	h _{FE} *	100	-	320	
DC Current Gain I _C =800mA, V _{CE} =1V	h _{FE}	40	-	-	
Collector-Emitter Saturation Voltage (I _C =800mA I _B =80mA)	V _{CE(S)}	-	-	0.5	V

NOTE :

*	P	Q
h _{FE}	100~200	160~320

LH8050PLTIG Series , S-LH8050PLTIG Series

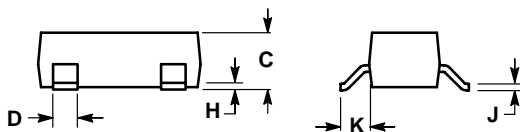
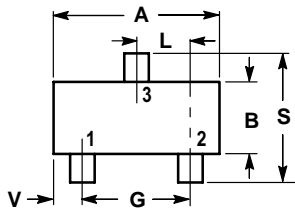
 Electrical Characteristic Curves ($T_A=25^\circ\text{C}$)


LH8050PLTIG Series , S-LH8050PLTIG Series

SOT-23

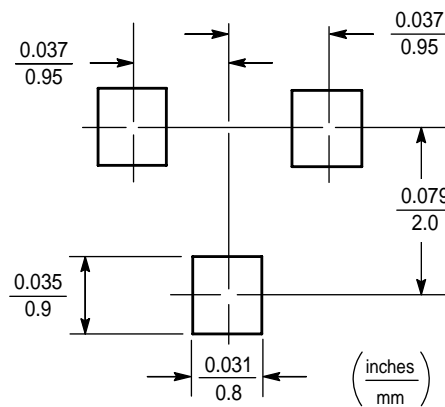
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

PIN 1. BASE
 2. EMITTER
 3. COLLECTOR



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